

# FMH11N90E

FUJI POWER MOSFET

## Super FAP-E<sup>3</sup> series

N-CHANNEL SILICON POWER MOSFET

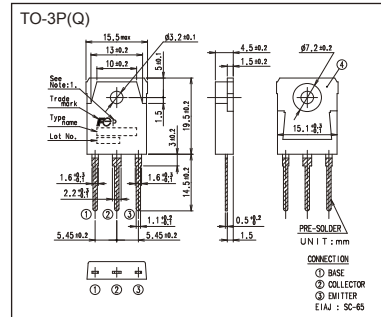
### Features

- Maintains both low power loss and low noise
- Lower  $R_{DS(on)}$  characteristic
- More controllable switching  $dv/dt$  by gate resistance
- Smaller  $V_{GS}$  ringing waveform during switching
- Narrow band of the gate threshold voltage ( $4.0 \pm 0.5V$ )
- High avalanche durability

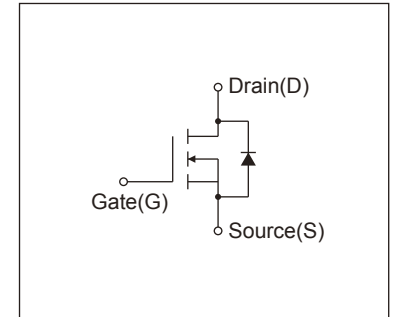
### Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

### Outline Drawings [mm]



### Equivalent circuit schematic



### Maximum Ratings and Characteristics

#### Absolute Maximum Ratings at $T_c=25^\circ C$ (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	$V_{DS}$	900	V	
	$V_{DSX}$	900	V	$V_{GS} = -30V$
Continuous Drain Current	$I_D$	$\pm 11$	A	
Pulsed Drain Current	$I_{DP}$	$\pm 44$	A	
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	$I_{AR}$	11	A	Note*1
Non-Repetitive Maximum Avalanche Energy	$E_{AS}$	811.9	mJ	Note*2
Repetitive Maximum Avalanche Energy	$E_{AR}$	28.5	mJ	Note*3
Peak Diode Recovery $dV/dt$	$dV/dt$	2.2	kV/ $\mu s$	Note*4
Peak Diode Recovery $-di/dt$	$-di/dt$	100	A/ $\mu s$	Note*5
Maximum Power Dissipation	$P_D$	2.5	W	$T_a=25^\circ C$
		285		$T_c=25^\circ C$
Operating and Storage Temperature range	$T_{ch}$	150	$^\circ C$	
	$T_{stg}$	-55 to +150	$^\circ C$	

#### Electrical Characteristics at $T_c=25^\circ C$ (unless otherwise specified)

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	900	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$I_D=250\mu A, V_{DS}=V_{GS}$	3.5	4.0	4.5	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=900V, V_{GS}=0V$	-	-	25	$\mu A$
		$V_{DS}=720V, V_{GS}=0V$	-	-	250	
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 30V, V_{DS}=0V$	-	10	100	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	$I_D=5.5A, V_{GS}=10V$	-	0.83	1.0	$\Omega$
Forward Transconductance	$g_{fs}$	$I_D=5.5A, V_{DS}=25V$	6.5	13	-	S
Input Capacitance	$C_{iss}$	$V_{DS}=25V$	-	2300	3450	pF
Output Capacitance	$C_{oss}$	$V_{GS}=0V$	-	200	300	
Reverse Transfer Capacitance	$C_{rss}$	$f=1MHz$	-	15	22.5	
Turn-On Time	$t_{d(on)}$	$V_{cc}=600V$	-	37	56	ns
	$t_r$	$V_{GS}=10V$	-	32	48	
Turn-Off Time	$t_{d(off)}$	$I_D=5.5A$	-	124	186	
	$t_f$	$R_G=20\Omega$	-	34	51	
Total Gate Charge	$Q_G$	$V_{cc}=450V$	-	60	90	nC
Gate-Source Charge	$Q_{GS}$	$I_D=11A$	-	17	26	
Gate-Drain Charge	$Q_{GD}$	$V_{GS}=10V$	-	23	35	
Gate-Drain Crossover Charge	$Q_{SW}$		-	7	11	
Avalanche Capability	$I_{AV}$	$L=4.92mH, T_{ch}=25^\circ C$	11	-	-	A
Diode Forward On-Voltage	$V_{SD}$	$I_F=11A, V_{GS}=0V, T_{ch}=25^\circ C$	-	0.90	1.35	V
Reverse Recovery Time	$t_{rr}$	$I_F=11A, V_{GS}=0V$	-	2.0	-	$\mu s$
Reverse Recovery Charge	$Q_{rr}$	$-di/dt=100A/\mu s, T_{ch}=25^\circ C$	-	20	-	$\mu C$

#### Thermal Characteristics

Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	$R_{th(ch-c)}$	Channel to case			0.4386	$^\circ C/W$
	$R_{th(ch-a)}$	Channel to ambient			50.0	$^\circ C/W$

Note \*1 :  $T_{ch} \leq 150^\circ C$

Note \*2 : Stating  $T_{ch}=25^\circ C, I_{AS}=4.4A, L=76.9mH, V_{cc}=90V, R_G=10\Omega$   
 $E_{AS}$  limited by maximum channel temperature and avalanche current.  
 See to 'Avalanche current' graph.

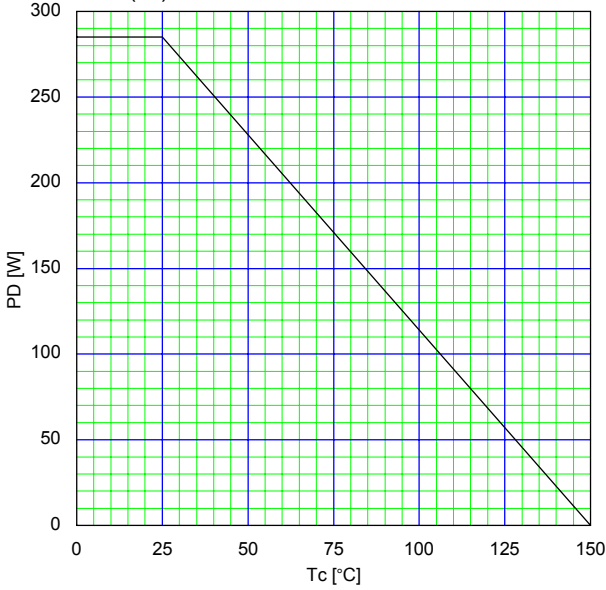
Note \*3 : Repetitive rating : Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal impedance' graph.

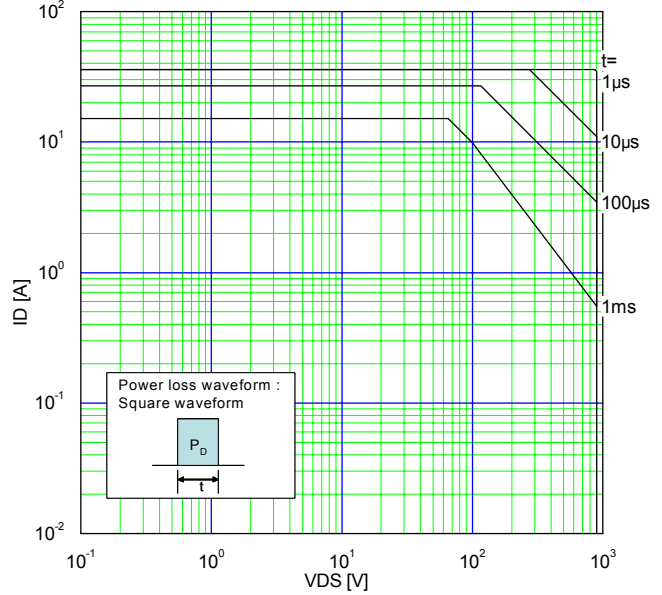
Note \*4 :  $I_F \leq I_D, -di/dt=100A/\mu s, V_{cc} \leq BV_{DSS}, T_{ch} \leq 150^\circ C$ .

Note \*5 :  $I_F \leq I_D, dv/dt=2.2kV/\mu s, V_{cc} \leq BV_{DSS}, T_{ch} \leq 150^\circ C$ .

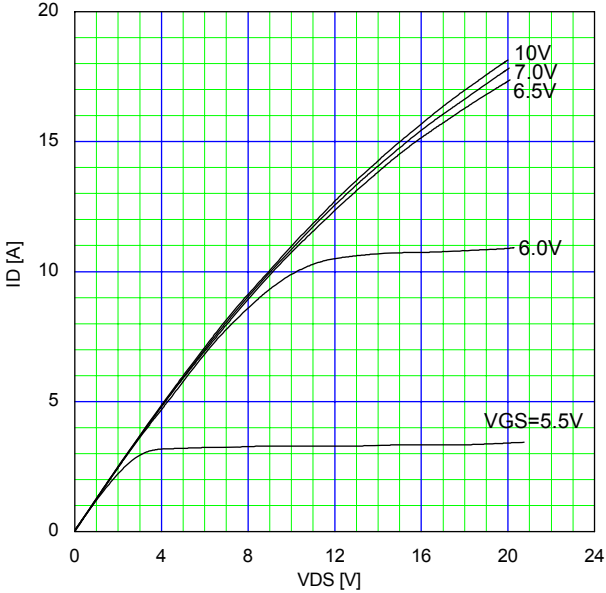
Allowable Power Dissipation  
 $P_D = f(T_c)$



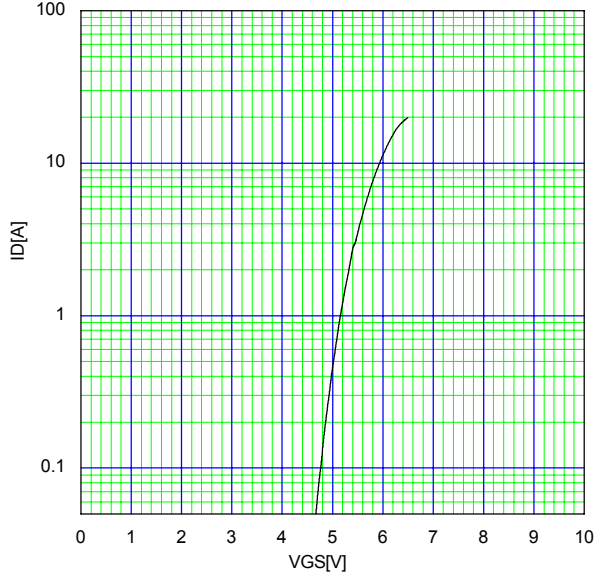
Safe Operating Area  
 $I_D = f(V_{DS})$ : Duty=0 (Single pulse),  $T_c = 25^\circ\text{C}$



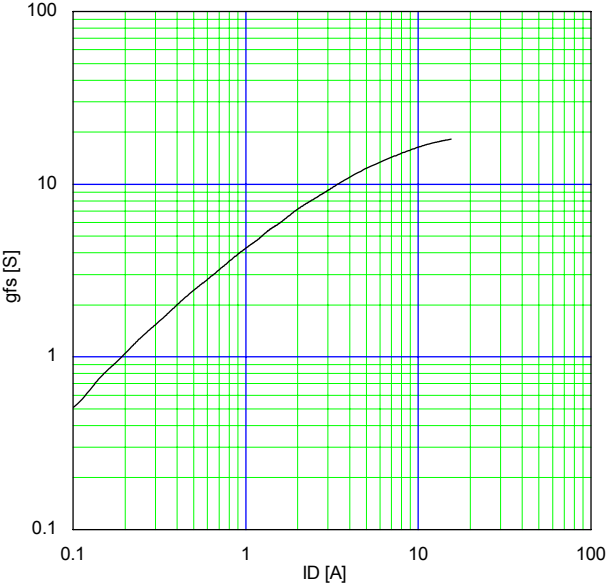
Typical Output Characteristics  
 $I_D = f(V_{DS})$ : 80 μs pulse test,  $T_{ch} = 25^\circ\text{C}$



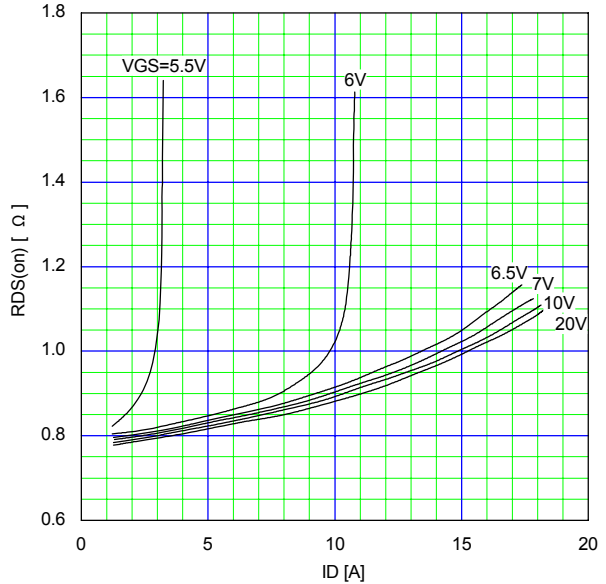
Typical Transfer Characteristic  
 $I_D = f(V_{GS})$ : 80 μs pulse test,  $V_{DS} = 25\text{V}$ ,  $T_{ch} = 25^\circ\text{C}$



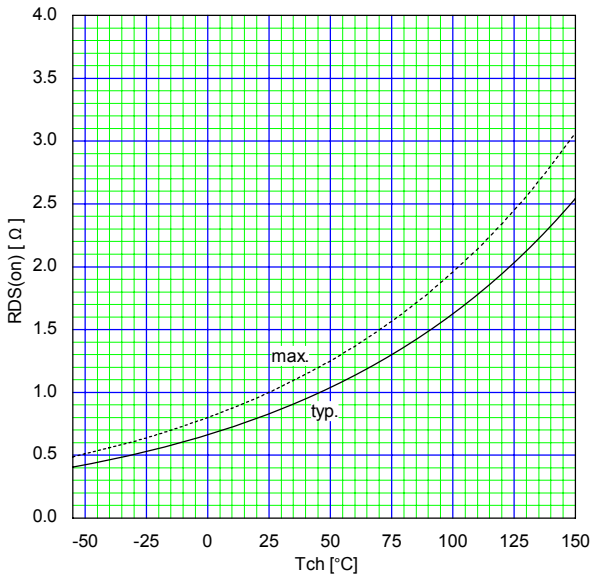
Typical Transconductance  
 $g_{fs} = f(I_D)$ : 80 μs pulse test,  $V_{DS} = 25\text{V}$ ,  $T_{ch} = 25^\circ\text{C}$



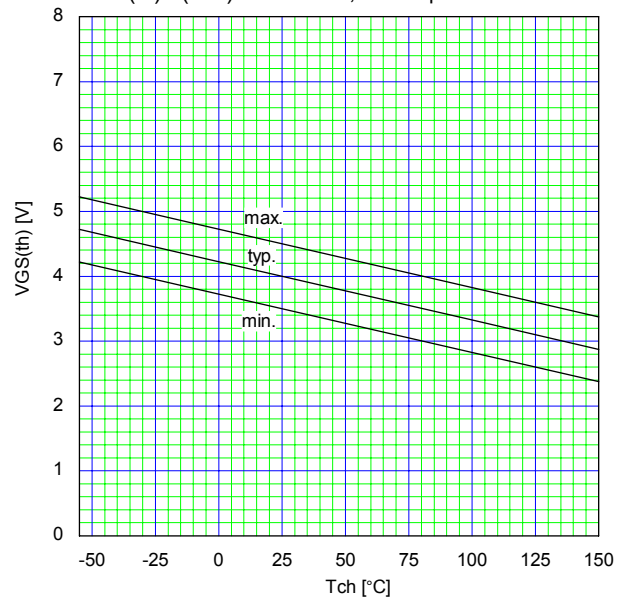
Typical Drain-Source on-state Resistance  
 $R_{DS(on)} = f(I_D)$ : 80 μs pulse test,  $T_{ch} = 25^\circ\text{C}$



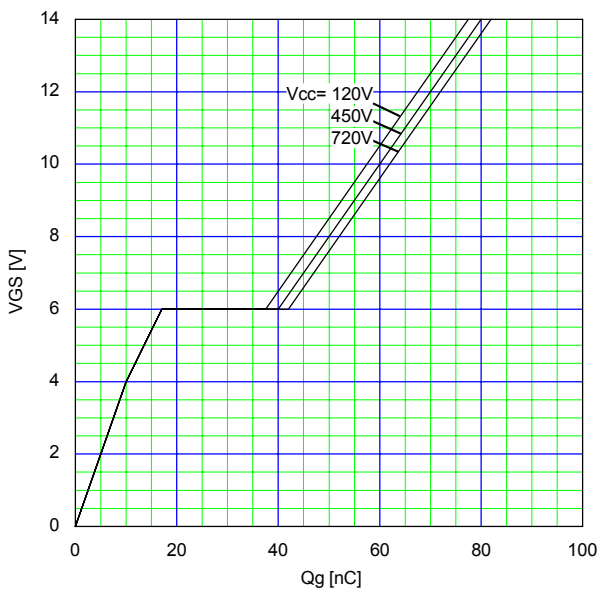
Drain-Source On-state Resistance  
 $R_{DS(on)} = f(T_{ch})$ ;  $I_D = 5.5A, V_{GS} = 10V$



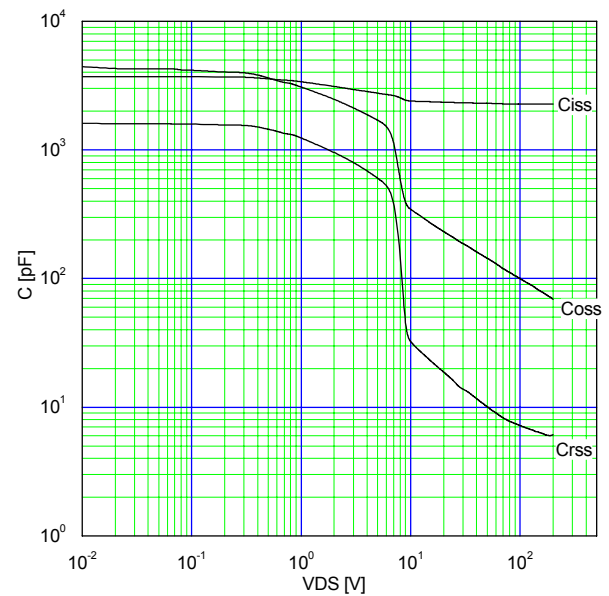
Gate Threshold Voltage vs.  $T_{ch}$   
 $V_{GS(th)} = f(T_{ch})$ ;  $V_{DS} = V_{GS}, I_D = 250\mu A$



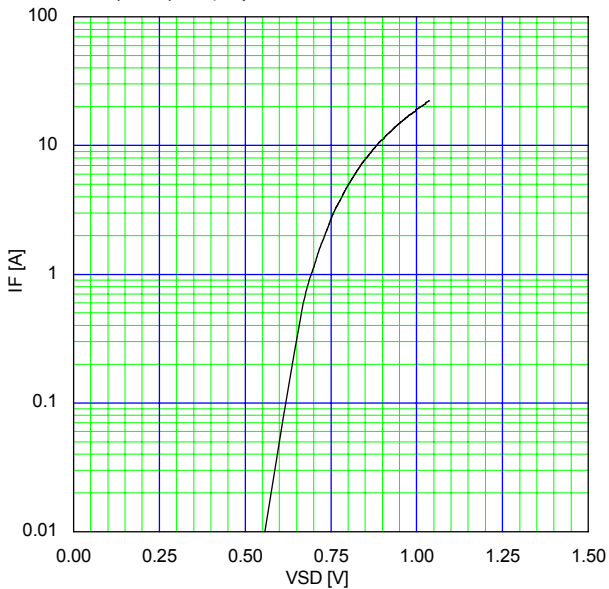
Typical Gate Charge Characteristics  
 $V_{GS} = f(Q_g)$ ;  $I_D = 11A, T_{ch} = 25^\circ C$



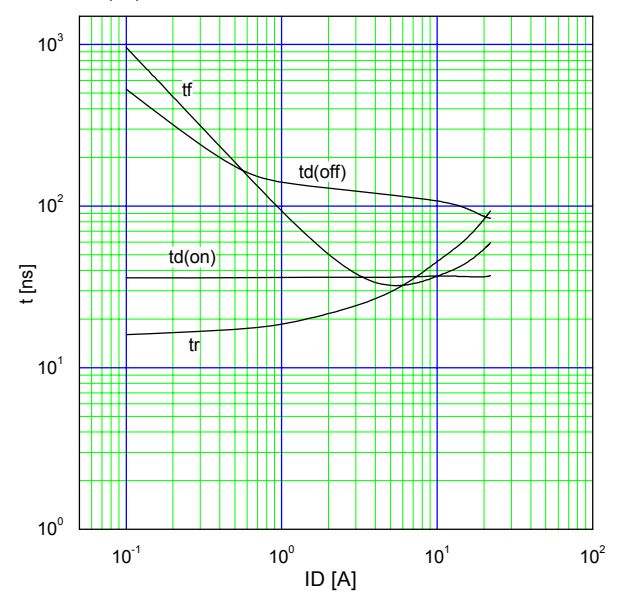
Typical Capacitance  
 $C = f(V_{DS})$ ;  $V_{GS} = 0V, f = 1MHz$



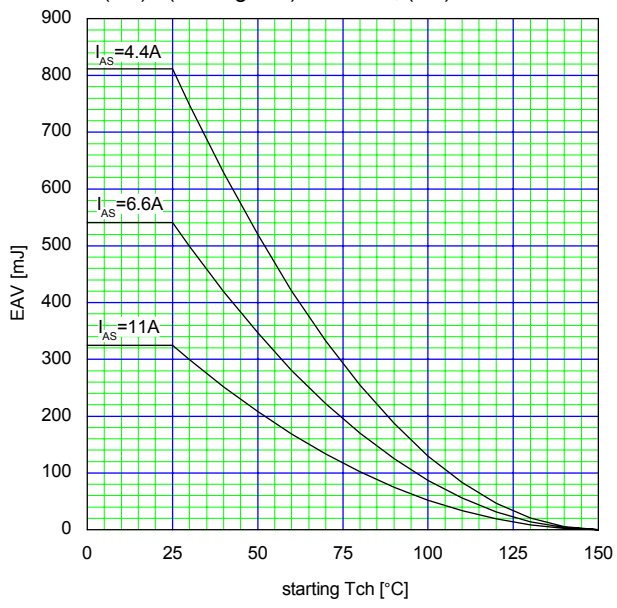
Typical Forward Characteristics of Reverse Diode  
 $I_F = f(V_{SD})$ ;  $80\mu s$  pulse test,  $T_{ch} = 25^\circ C$



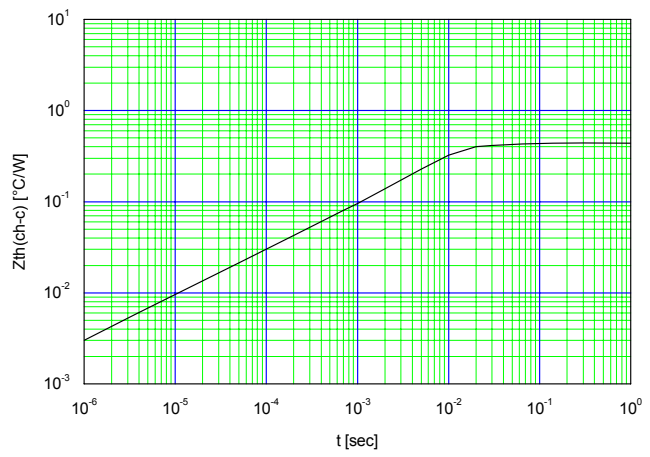
Typical Switching Characteristics vs.  $I_D$   
 $t = f(I_D)$ ;  $V_{cc} = 600V, V_{GS} = 10V, R_G = 20\Omega$



Maximum Avalanche Energy vs. starting Tch  
 $E(AV)=f(\text{starting Tch}):V_{CC}=90V, I(AV)\leq 11A$



Maximum Transient Thermal Impedance  
 $Z_{th}(ch-c)=f(t):D=0$



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